

ABSTRACT OF THE DISCLOSURE

A suspended resist bridge suitable for lithographically patterning MR sensors having trackwidths narrower than 0.2 micron is fabricated using the method of the present invention. First, PMGI is spun onto a substrate to form a first thin resist layer. Next, PMMA is spun onto the first resist layer to form a second resist layer. The PMMA layer is exposed to an electron beam to pattern the trackwidth of the MR sensors. E-beam exposed PMMA is then developed in an IPA solution. The resist structure is then placed in a basic solution for dissolving PMGI, which results in a fully undercut resist bridge that is used for patterning the MR sensors.